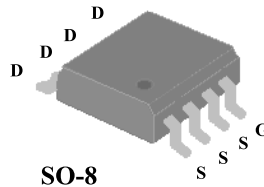




- ▼ Simple Drive Requirement
- ▼ Low On-resistance
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant

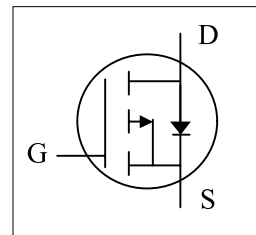


BV_{DSS}	-30V
$R_{DS(ON)}$	20m Ω
I_D	-9A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SO-8 package is widely preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	- 30	V
V_{GS}	Gate-Source Voltage	\pm 20	V
$I_D@T_A=25^\circ C$	Continuous Drain Current ³	-9	A
$I_D@T_A=70^\circ C$	Continuous Drain Current ³	-7.3	A
I_{DM}	Pulsed Drain Current ¹	-50	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	50	$^\circ C/W$